

N-Ch 150V Fast Switching MOSFETs

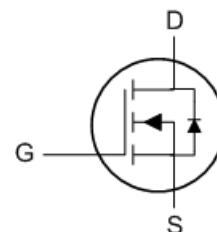
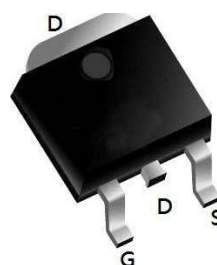
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary


BVDSS	RDSON	ID
150V	240mΩ	10A

Description

The UD10N15 is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications. The UD10N15 meet the RoHS and Green Product requirement with full function reliability approved.

TO252 Pin Configuration

Absolute Maximum Ratings (TA = 25°C, unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	150	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T _C =25°C	I_D	10	A
	T _C =100°C		5.4	
Pulsed Drain Current ¹		I_{DM}	35	A
Single Pulse Avalanche Energy ²		EAS	9.8	mJ
Total Power Dissipation	T _C =25°C	P_D	40.3	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ³	R_{θJA}	62	°C/W
Thermal Resistance from Junction-to-Case	R_{θJC}	3.1	°C/W

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	150	-	-	V
Gate-body Leakage current		I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T _J =25°C	I _{DSS}	V _{DS} = 150V, V _{GS} = 0V	-	-	1	μA
	T _J =100°C			-	-	100	
Gate-Threshold Voltage		V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.2	2	2.5	V
Drain-Source on-Resistance ⁴		R _{DS(on)}	V _{GS} = 10V, I _D = 4A	-	240	300	mΩ
Forward Transconductance ⁴		g _{fs}	V _{DS} = 10V, I _D = 4A	-	14.5	-	S
Dynamic Characteristics ⁵							
Input Capacitance		C _{iss}	V _{DS} = 75V, V _{GS} =0V, f =1MHz	-	465	-	pF
Output Capacitance		C _{oss}		-	23	-	
Reverse Transfer Capacitance		C _{rss}		-	14	-	
Gate Resistance		R _g	f =1MHz	-	2	-	Ω
Switching Characteristics ⁵							
Total Gate Charge		Q _g	V _{GS} = 10V,V _{DS} = 75V, I _D = 4A	-	14	-	nC
Gate-Source Charge		Q _{gs}		-	1.6	-	
Gate-Drain Charge		Q _{gd}		-	4	-	
Turn-on Delay Time		t _{d(on)}	V _{GS} =10V, V _{DD} =75V, R _G = 3Ω, I _D = 4A	-	5.8	-	ns
Rise Time		t _r		-	2.2	-	
Turn-off Delay Time		t _{d(off)}		-	16.9	-	
Fall Time		t _f		-	2.6	-	
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴		V _{SD}	I _S = 1A, V _{GS} = 0V	-	-	1.2	V
Continuous Source Current	T _C =25°C	I _S	-	-	-	10	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ\text{C}$.
2. The EAS data shows Max. rating . The test condition is $V_{DD} = 25V, V_{GS} = 10V, L = 0.4\text{mH}, I_{AS} = 7A$.
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

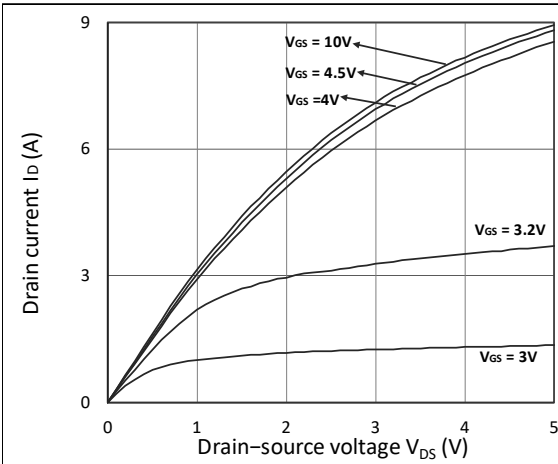


Figure 1. Output Characteristics

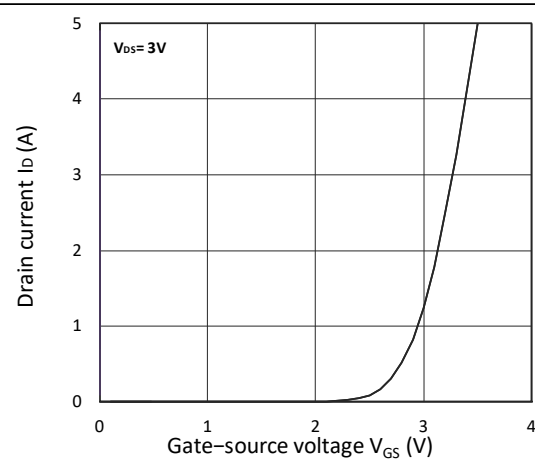


Figure 2. Transfer Characteristics

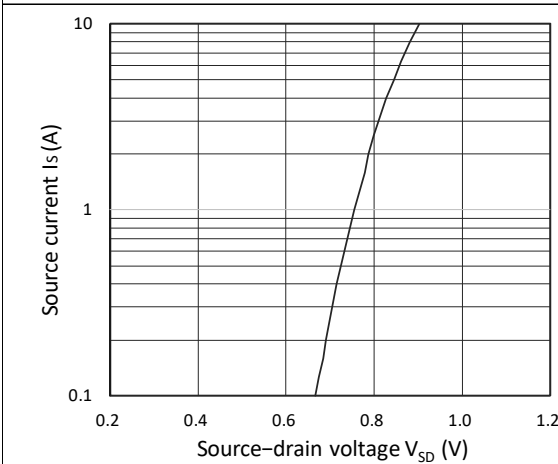


Figure 3. Forward Characteristics of Reverse

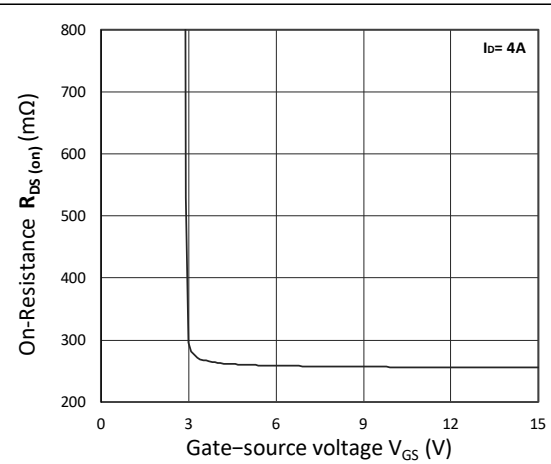


Figure 4. $R_{DS(on)}$ vs. V_{GS}

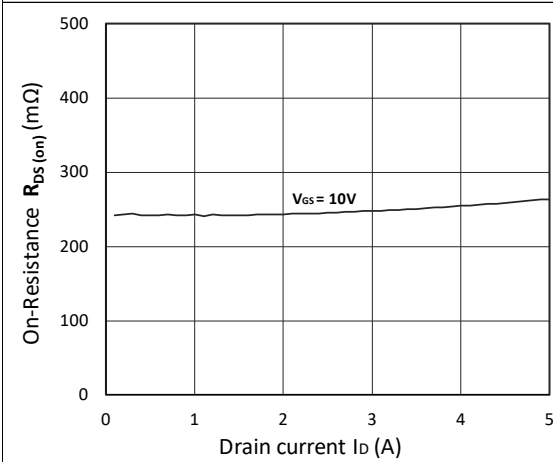


Figure 5. $R_{DS(on)}$ vs. I_D

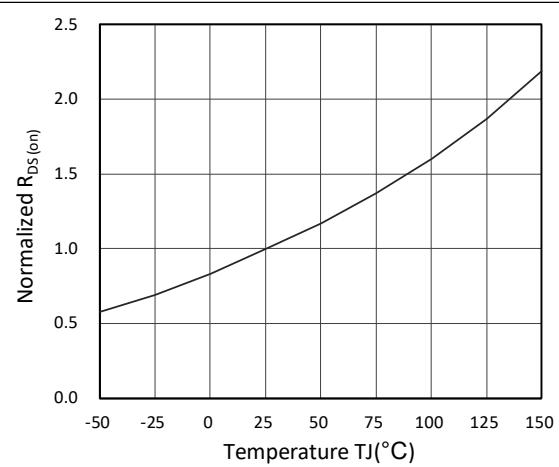


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

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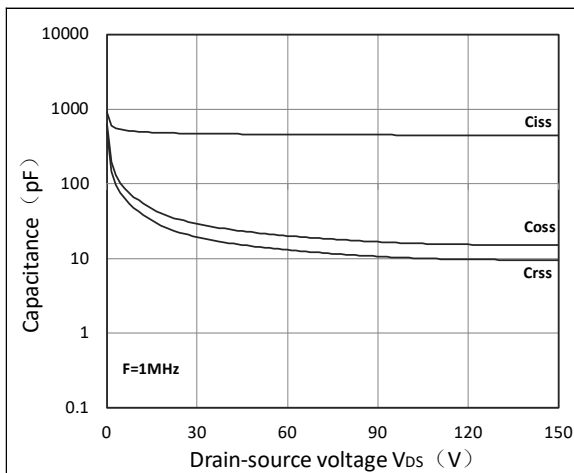


Figure 7. Capacitance Characteristics

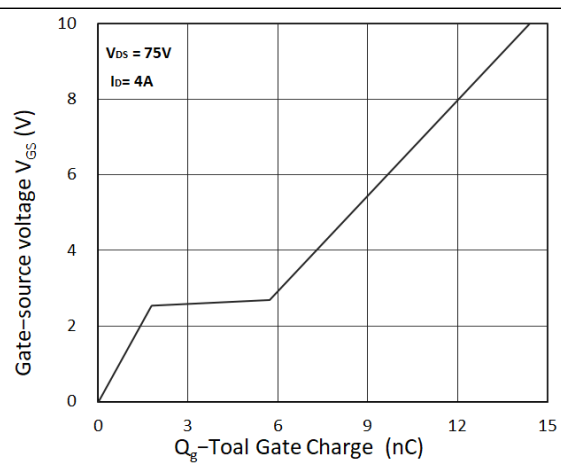


Figure 8. Gate Charge Characteristics

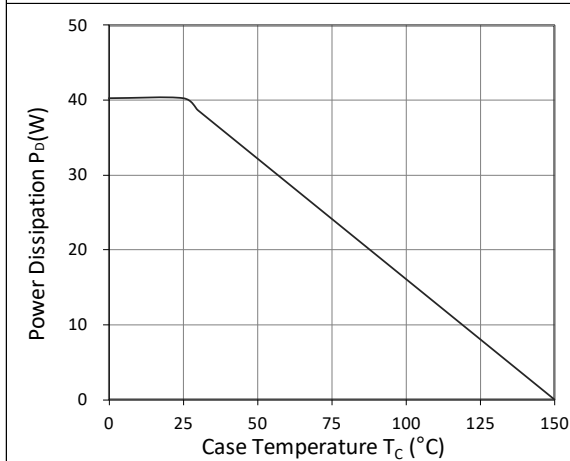


Figure 9. Power Dissipation

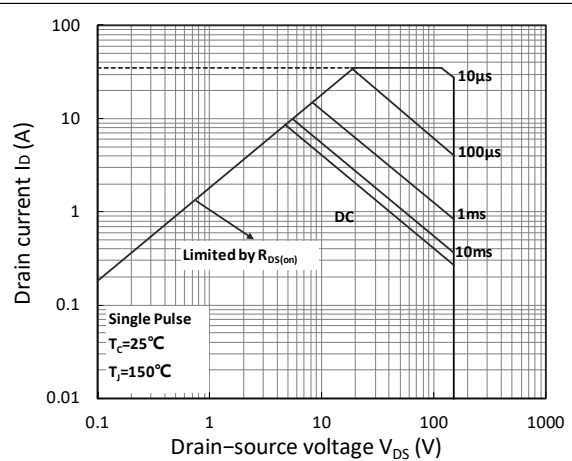


Figure 10. Safe Operating Area

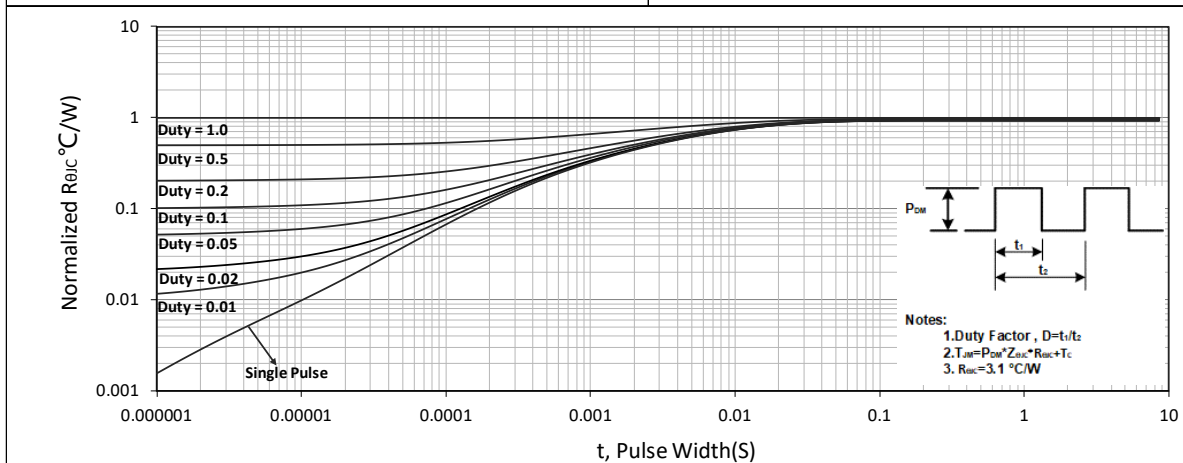
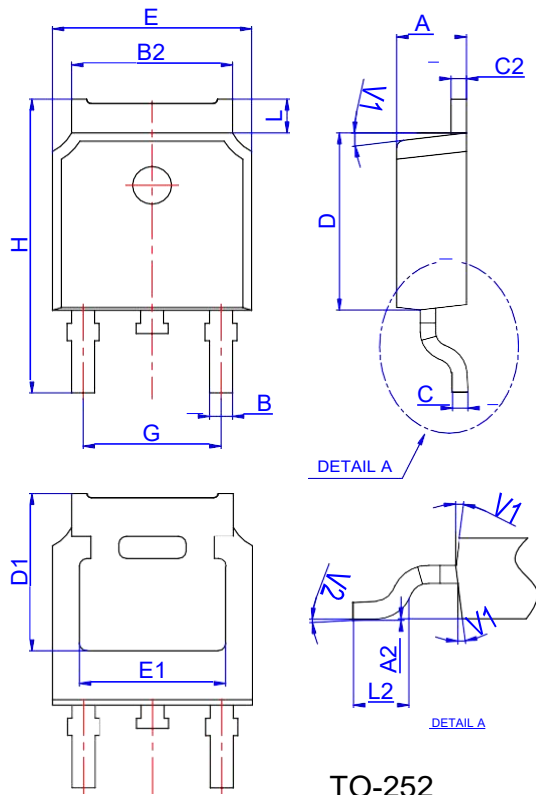


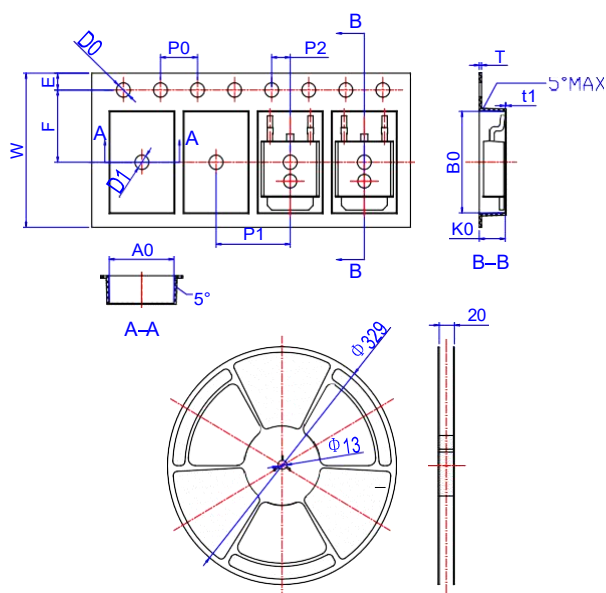
Figure 11. Normalized Maximum Transient Thermal Impedance

Package Mechanical Data-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252-4R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583